

## COMPLEMENTARY SILICON POWER TRANSISTORS

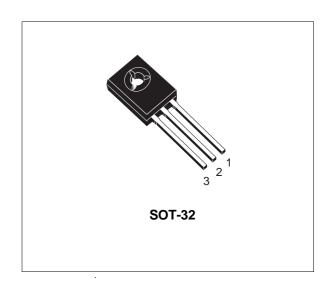
- STMicroelectronics PREFERRED SALESTYPE
- COMPLEMENTARY PNP NPN DEVICES

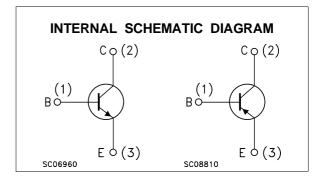
#### **DESCRIPTION**

The BD433, BD435, and BD437 are silicon epitaxial-base NPN power transistors in Jedec SOT-32 plastic package, intented for use in medium power linear and switching applications.

The BD433 is especially suitable for use in car-radio output stages.

The complementary PNP types are BD434, BD436, and BD438 respectively.





### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter		Value			
		NPN	BD433	BD435	BD437	
		PNP	BD434	BD436	BD438	
V <sub>CBO</sub>	Collector-Base Voltage (I <sub>E</sub> = 0)		22	32	45	V
Vces	Collector-Emitter Voltage (V <sub>BE</sub> = 0)		22	32	45	V
V <sub>CEO</sub>	Collector-Emitter Voltage (I <sub>B</sub> = 0)		22	32	45	V
V <sub>EBO</sub>	Emitter-Base Voltage (I <sub>C</sub> = 0)			5		V
Ic	Collector Current			4		Α
I <sub>CM</sub>	Collector Peak Current (t ≤ 10 ms)			7		Α
Ι <sub>Β</sub>	Base Current			1		Α
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> ≤ 25 °C			36		W
T <sub>stg</sub>	Storage Temperature		-65 to 150			°C
Tj	Max. Operating Junction Temperature			150		°C

For PNP types voltage and current values are negative.

February 2003

### BD433 BD434 BD435 BD436 BD437 BD438

#### THERMAL DATA

R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	3.5	°C/W	
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	100	°C/W	

### **ELECTRICAL CHARACTERISTICS** (T<sub>case</sub> = 25 °C unless otherwise specified)

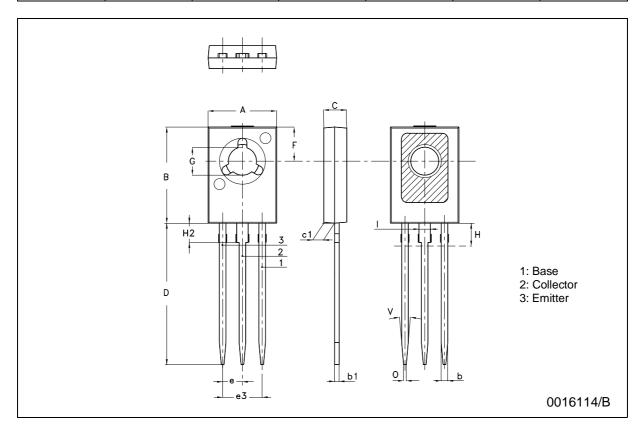
Symbol	Parameter	Test	Conditions	Min.	Тур.	Max.	Unit
Ісво	Collector Cut-off Current (I <sub>E</sub> = 0)	for <b>BD433/434</b> for <b>BD435/436</b> for <b>BD437/438</b>	$V_{CB} = 32 \text{ V}$			100 100 100	μΑ μΑ μΑ
I <sub>CES</sub>	Collector Cut-off Current (V <sub>BE</sub> = 0)	for <b>BD433/434</b> for <b>BD435/436</b> for <b>BD437/438</b>	$V_{CE} = 32 \text{ V}$			100 100 100	μΑ μΑ μΑ
I <sub>EBO</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 5 V				1	mA
V <sub>CEO(sus)</sub> *	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 100 mA	for <b>BD433/434</b> for <b>BD435/436</b> for <b>BD437/438</b>	22 32 45			V V V
VCE(sat)*	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2 A	I <sub>B</sub> = 0.2 A for <b>BD433/434</b> for <b>BD435/436</b> for <b>BD437/438</b>		0.2 0.2 0.2	0.5 0.5 0.6	V V V
V <sub>BE</sub> *	Base-Emitter Voltage	I <sub>C</sub> = 10 mA I <sub>C</sub> = 2 A	$V_{CE} = 5 \text{ V}$ $V_{CE} = 1 \text{ V}$ for BD433/434 for BD435/436 for BD437/438		0.58	1.1 1.1 1.2	V V V
h <sub>FE</sub> *	DC Current Gain	I <sub>C</sub> = 10 mA I <sub>C</sub> = 500 mA I <sub>C</sub> = 2 A	V <sub>CE</sub> = 5 V for <b>BD433/434</b> for <b>BD435/436</b> for <b>BD437/438</b> V <sub>CE</sub> = 1 V V <sub>CE</sub> = 1 V for <b>BD433/434</b> for <b>BD435/436</b>	40 40 30 85 50 50 40	130 130 130 140		
h <sub>FE1</sub> /h <sub>FE2</sub> *	Matched Pair	I <sub>C</sub> = 500 mA	V <sub>CE</sub> = 1 V			1.4	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> = 250 mA	V <sub>CE</sub> = 1 V	3			MHz

<sup>\*</sup> Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

2/4

# SOT-32 (TO-126) MECHANICAL DATA

DIM.		mm			inch	
DIN.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α	7.4		7.8	0.291		0.307
В	10.5		10.8	0.413		0.425
b	0.7		0.9	0.028		0.035
b1	0.40		0.65	0.015		0.025
С	2.4		2.7	0.094		0.106
c1	1.0		1.3	0.039		0.051
D	15.4		16.0	0.606		0.630
е		2.2			0.087	
e3		4.4			0.173	
F		3.8			0.150	
G	3		3.2	0.118		0.126
Н			2.54			0.100
H2		2.15			0.084	
1		1.27			0.05	
0		0.3			0.011	
V		10°			10°	



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a trademark of STMicroelectronics

© 2003 STMicroelectronics – Printed in Italy – All Rights Reserved STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States.

http://www.st.com

47/

## **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by STMicroelectronics manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H MJ15024/WS MJ15025/WS BC546/116 BC556/FSC BC557/116 BSW67A HN7G01FU-A(T5L,F,T NJVMJD148T4G NSVMMBT6520LT1G NTE187A NTE195A NTE2302 NTE2302 NTE2330 NTE2353 NTE316 IMX9T110 NTE63 NTE65 C4460 SBC846BLT3G 2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA1727TLP 2SA2126-E 2SB1202T-TL-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMC5AT148 2N2369ADCSM 2SB1202S-TL-E 2SC2412KT146S 2SC4618TLN 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E BC557B TTC012(Q) BULD128DT4 JANTX2N3810 Jantx2N5416 US6T6TR KSF350 068071B